

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) 08228/019001		Application Number 10/044,686	
				Applicant(s) Shiro SAKAI et al.			
				Filing Date January 11, 2002		Group Art Unit 1765 1700	

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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
F.H.	A1	6,030,848	02/29/2000	Yuge et al.	438	46	04/16/1997
↑	A2	5,929,466	07/27/1999	Ohba et al.	257	103	06/13/1997
↓	A3	5,900,650	05/04/1999	Nitta	257	94	07/02/1997
F.H.	A4	5,888,886	03/30/1999	Sverdlov et al.	438	505	06/30/1997

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
F.H.	A6	10-312971	11/24/1998	Japan	H01L	21/205		✓
↑	A7	2000-21789	01/21/2000	Japan	H01L	21/205		✓
↓	A8	11-354839	12/24/1999	Japan	H01L	33/00		✓
↓	A9	11-354840	12/24/1999	Japan	H01L	33/00		✓
F.H.	A10	11-354842	12/24/1999	Japan	H01L	33/00		✓

OTHER DOCUMENTS <small>(Including Author, Title, Date, Pertinent Pages, Etc.)</small>		
F.H.	A11	English/Japanese Notice of Grounds For Rejection, Japanese Patent Application Serial No. 2000-227963, 7 pages
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EXAMINER <i>[Signature]</i>	DATE CONSIDERED 5/17/05
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	Filing Date January 11, 2002	Group Art Unit 1765 1702	

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
F.H.	C1	11-145516	05/28/1999	Japan	H01L	33/00		✓
↑	C2	11-346032	12/14/1999	Japan	H01S	3/18		✓
↓	C3	11-346035	12/14/1999	Japan	H01S	3/18		✓
↕	C4	2000-91252	03/31/2000	Japan	H01L	21/205		✓
F.H.	C5	2000-91253	03/31/2000	Japan	H01L	21/205		✓

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

F <sub>1</sub> H.	C6	Patent Abstract of Japanese Patent No. JP11354839, published 12/24/1999, 1 page
F <sub>2</sub> H.	C7	Patent Abstract of Japanese Patent No. JP11354840, published 12/24/1999, 1 page

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							YES	NO
F.H.	D1	2000-357820	12/26/2000	Japan	H01L	33/00		✓
F.H.	D2	4-297023	10/21/1992	Japan	H01L	21/205		✓
F.H.	D3	EP 0 497 350 B2	08/05/1992	Europe	C30B	25/02		

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F.H.	D4	Patent Abstract of Japanese Patent No. JP11354842, published 12/24/1999, 1 page
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L. H. H. H.

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Applicant(s)

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F3

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F6

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F12

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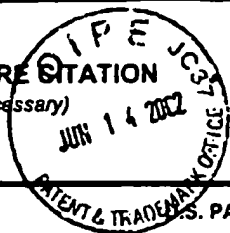
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<b>CIPE INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary) MAY 20 2002		Docket Number (Optional) 08228/019001	Application Number 10/044,686
		Applicant(s) Shiro SAKAI et al.	
		Filing Date January 11, 2002	Group Art Unit 1265/157
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER F.H.	G1	"Growth of high-quality GaN by low-pressure metal-organic vapour phase epitaxy (LP-MOVPE) from 3D islands and lateral overgrowth", H. Lahrech et al. N.H Elsevier Journal of Crystal Growth 205 (1999) 245-252, 8 pages	
	G2	"Optimization of Si/N Treatment Time of Sapphire Surface and Its Effect on the MOVPE GaN Overlayers", S. Haffouz et al. phys. stat. sol. (a) 176, 677 (1999), 5 pages	
	G3	"Influence of in situ sapphire surface preparation and carrier gas on the growth mode of GaN in MOVPE" P. Vennegues et al. N.H. Elsevier Journal of Crystal Growth 187 (1998) 167-177, 11 pages	
	G4	"Fabrication and Characterization of Low Defect Density GaN Using Facet Controlled Epitaxial Lateral Overgrowth (FACELO)" K. Hiramatsu et al. The Tenth International Conference on Metalorganic Vapor Phase Epitaxy June 5-9, 2000 Hokkaido University Conference Hall, Sapporo, Japan (pages 289-300) (5 pages)	
	G5	"Preparation of conductive ZnO:Al films by a facing target system with a strong magnetic field" Kikuo Tominaga et al. Thin Solid Films 253 (1994) pages 9-13 Elsevier Science S.A. (5 pages)	
	G6	"p-Type Electrical Conduction in ZnO Thin Films by Ga and N Codoping" Matthew Joseph et al. Japanese Journal of Applied Physics, Vol. 38 (1999), pages L1205-L1207 (3 pages)	
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# INFORMATION DISCLOSURE CITATION

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Shiro SAKAI et al.

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January 11, 2002

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EH	A1	5,332,697	07/26/1994	Smith et al.	437	242	10/16/1991
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EH	A7	"Drastic Reduction of the Dislocation Density in GaN Films by Anti-Surfactant-Mediated Dot Formation"; M. TAKEUCHI et al., Workbook, The Tenth International Conference on Metalorganic Vapor Phase Epitaxy, June 5-9, 2000, Hokkaido University Conference Hall, Sapporo, Japan, 3 pages

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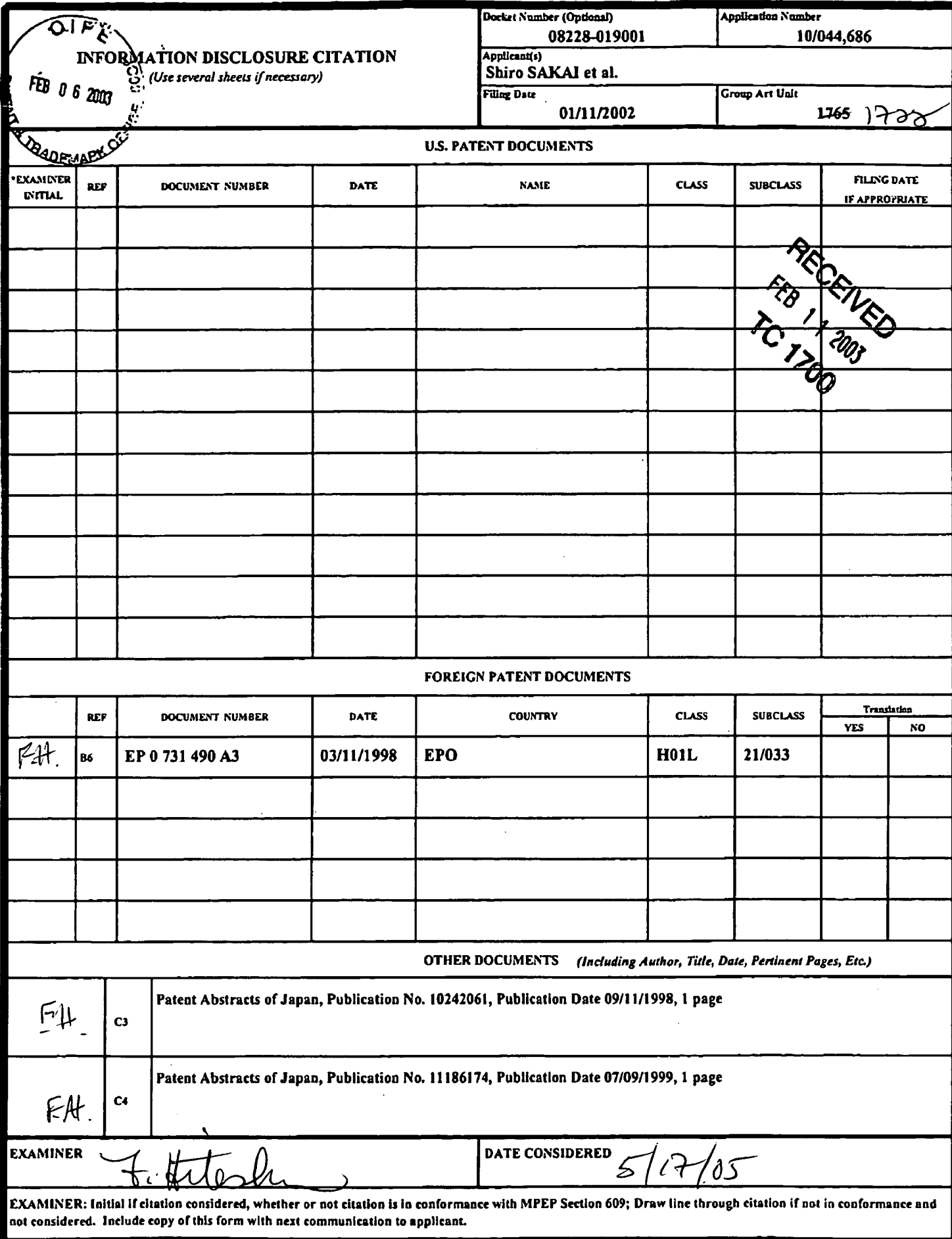
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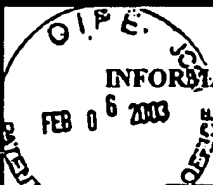










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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

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<b>F24</b>	<b>C7</b>	European Search Report dated 11/11/2002, 4 pages
<b>F11</b>	<b>C8</b>	European Search Report dated 01/08/2003, 3 pages

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Applicant(s)

Shiro SAKAI, et al.

Filing Date

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	A2	5,874,747	02/23/1999	Redwing et al.	257	77	02/05/1996
	A3	6,103,604	08/15/2000	Bruno et al.	438	584	02/10/1997
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	A7	6,429,102 B1	08/06/2002	Tsai et al.	438	508	02/03/2000
	A8	6,455,337 B1	09/24/2002	Sverdlov	438	22	06/27/2001
	A9	6,465,808 B2	10/15/2002	Lin	257	81	01/11/2001
	A10	2002/0036286 A1	03/28/2002	Ho et al.	257	11	05/15/2000
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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
F.H.	A12	JP407263408A	10/13/1995	Japan	H01L	021/3065	✓	
F.H.	A13	WO98/42030	09/24/1998	PCT	H01L	33/00		✓
F.H.	A14	WO98/44569	10/08/1998	PCT	H01L	33/00		✓

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F.H.	A15	European Search Report dated 11/27/2003 (4 pages)

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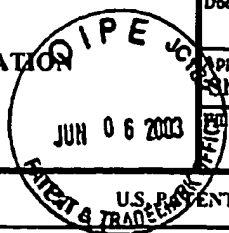
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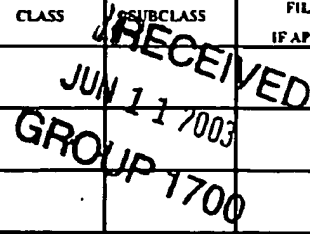
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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
FA	A1	4-288871	08/03/1993	Japan	HO1L	21/469		✓
FA	A2	9-17975	01/17/1997	Japan	HO1L	27/108		✓
FA	A3	10-163525	06/19/1998	Japan	HO1L	33/00		✓
FA	A4	EP 0 961 328 A2	12/01/1999	Europe	HO1L	33/00		

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Pat	A5	Japanese Patent Application Serial No. 091100294 Office Action dated March 14, 2003
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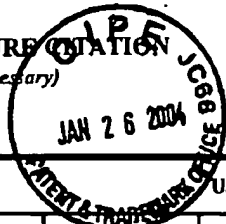
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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
<b>ETH</b>	<b>A1</b>	<b>2003/0178634 A1</b>	<b>09/25/2003</b>	<b>Koide</b>	<b>H01L</b>	<b>33/00</b>	<b>03/20/2003</b>

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							YES	NO

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